

TOSHIBA

MIG10Q806H/HA

TOSHIBA INTEGRATED IGBT MODULE SILICON N CHANNEL IGBT

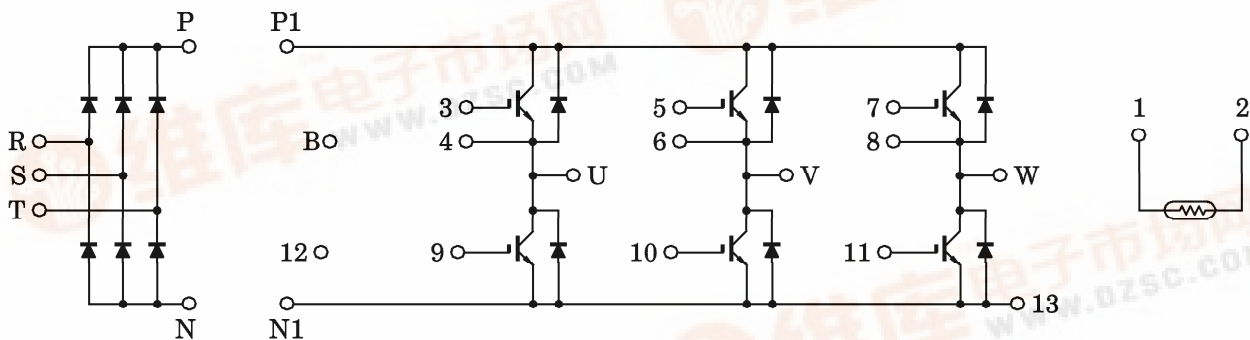
MIG10Q806H, MIG10Q806HA

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- Integrates Inverter, Converter Power Circuits and Thermistor in One Package.
- Output (Inverter Stage) : 3 ϕ 10 A / 1200 V IGBT
- Input (Converter Stage) : 3 ϕ 15 A / 1600 V Silicon Rectifier
- The Electrodes are Isolated from Case.
- Outline
 - MIG10Q806H : 2-108E5A
 - MIG10Q806HA : 2-108E6A
- Weight : 190 g

EQUIVALENT CIRCUIT

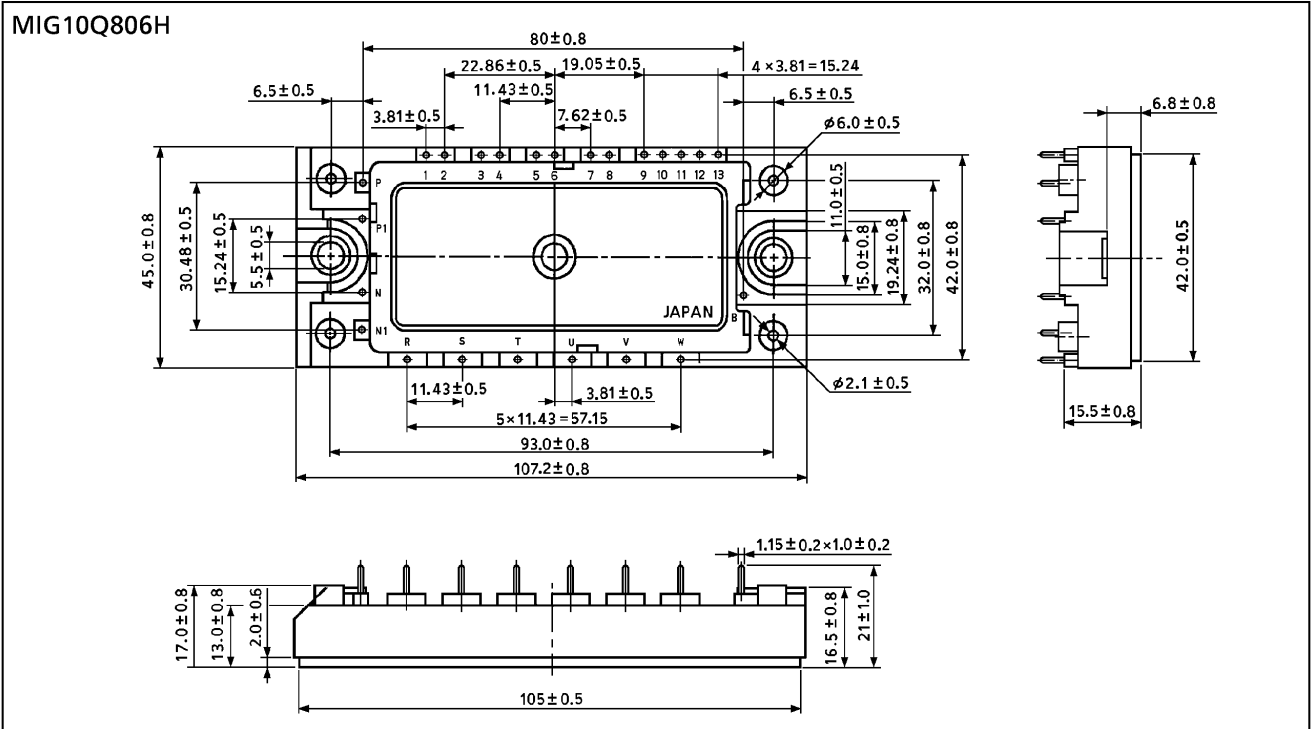


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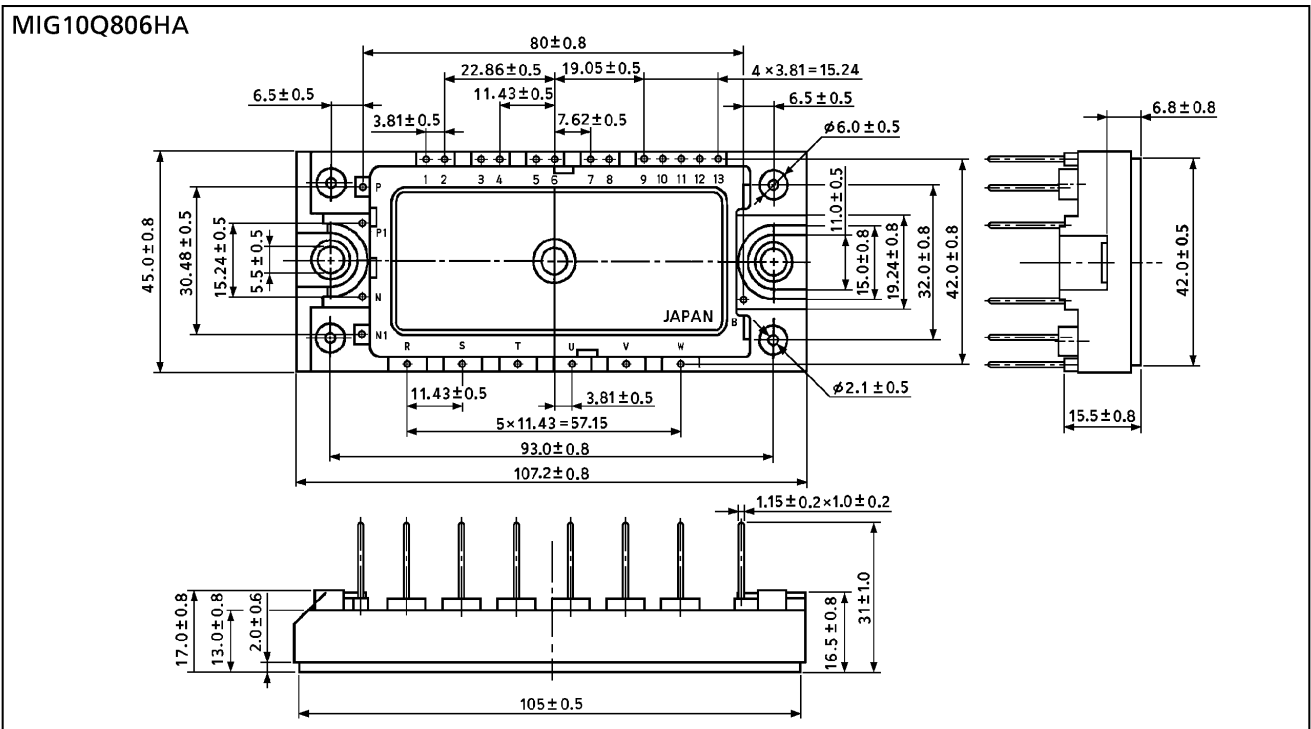
Package Dimension

Unit : mm



2-108E5A

Unit : mm



2-108E6A

MAXIMUM RATINGS (Ta = 25°C)

STAGE	CHARACTERISTIC	SYMBOL	RATING	UNIT	
Inverter	Collector-Emitter Voltage	V _{CES}	1200	V	
	Gate-Emitter Voltage	V _{GES}	±20	V	
	Collector Current	DC	I _C	15 / 10	A
		1 ms	I _{CP}	30 / 20	A
	Forward Current	DC	I _F	10	A
		1 ms	I _{FM}	20	A
Collector Power Dissipation (Tc = 25°C)		P _C	82	W	
Converter	Repetitive Peak Reverse Voltage	V _R RM	1600	V	
	Average Output Rectified Current	I _O	15	A	
	Peak One Cycle Surge Forward Current (50 Hz, Non-Repetitive)	I _F SM	250	A	
Module	Junction Temperature	T _j	150	°C	
	Storage Temperature Range	T _{stg}	-40~125	°C	
	Isolation Voltage	V _{Isol}	2500 (AC 1 minute)	V	
	Screw Torque	—	6	N·m	

(25°C / 80°C)
(25°C / 80°C)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

a. Inverter stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0$	—	—	± 500	nA		
Collector Cut-Off Current		I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0$	—	—	0.5	mA		
Gate-Emitter Cut-Off Voltage		$V_{GE(\text{off})}$	$I_C = 10\text{ mA}, V_{CE} = 5\text{ V}$	—	6.0	—	V		
Collector-Emitter Saturation Voltage		$V_{CE(\text{sat})}$	$I_C = 10\text{ A}$	—	2.8	3.2	V		
			$V_{GE} = 15\text{ V}$					$T_j = 25^\circ\text{C}$	
		C_{ies}	$V_{CE} = 10\text{ V}, V_{GE} = 0,$ $f = 1\text{ MHz}$	—	1200	—	pF		
Switching Time	Rise Time	t_r	$V_{CC} = 600\text{ V}$ $I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 120\ \Omega$ $T_j = 125^\circ\text{C}$ (Note 1)	—	0.07	0.15	μs		
	Turn-On Time	t_{on}						0.15	0.30
	Fall Time	t_f						0.07	0.10
	Turn-Off Time	t_{off}						0.60	0.90
Forward Voltage		V_F	$I_F = 10\text{ A}, V_{GE} = 0$	—	2.0	2.8	V		
Reverse Recovery Time		t_{rr}	$I_F = 10\text{ A}, V_{GE} = -10\text{ V}$ $di/dt = 200\text{ A}/\mu\text{s}$	—	0.10	0.25	μs		
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.52	$^\circ\text{C}/\text{W}$		
			Diode	—	—	1.5			

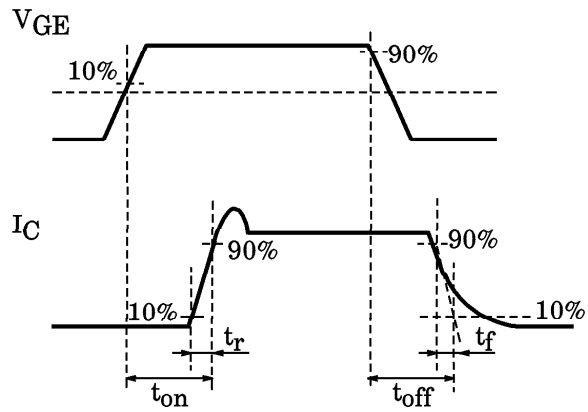
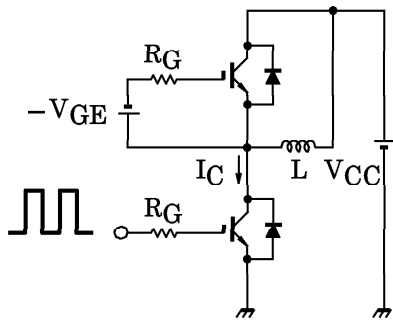
b. Converter stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Reverse Current		I_{RRM}	$V_{RRM} = 1600\text{ V}$	—	—	50	μA
Peak Forward Voltage		V_{FM}	$I_{FM} = 15\text{ A}$	—	1.05	1.20	V
Peak One Cycle Surge Forward Current		I_{FSM}	50 Hz sine-half-wave	250	—	—	A
Thermal Resistance		$R_{th(j-c)}$	—	—	—	1.90	$^\circ\text{C}/\text{W}$

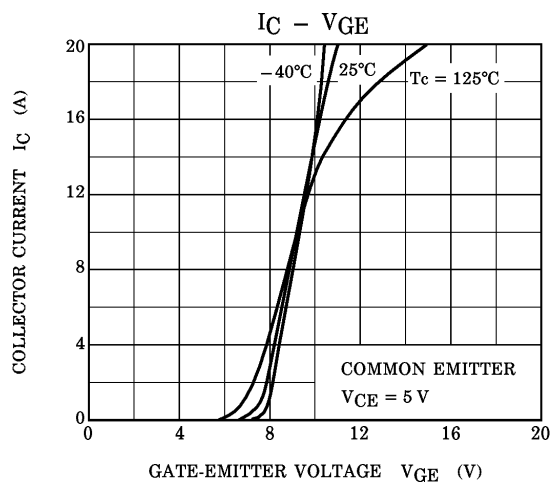
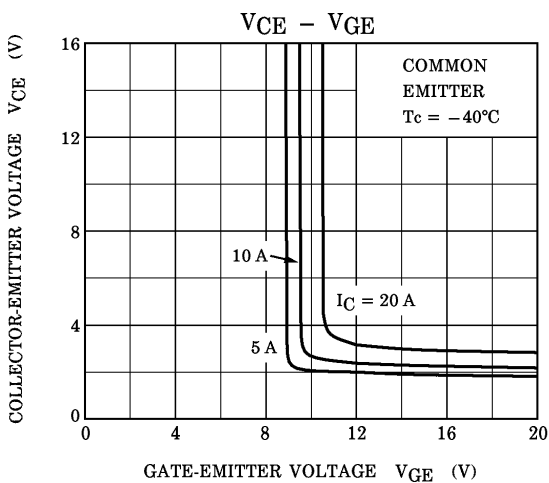
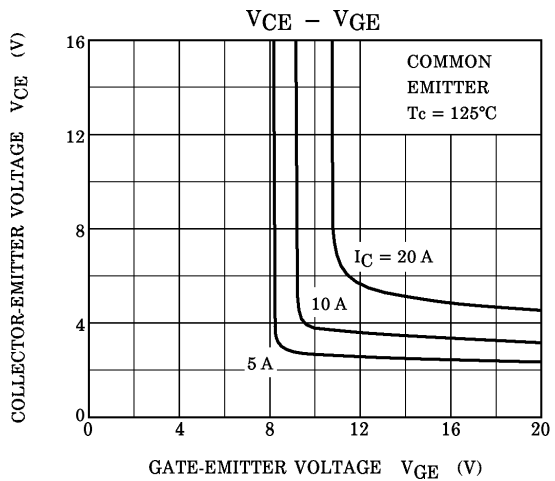
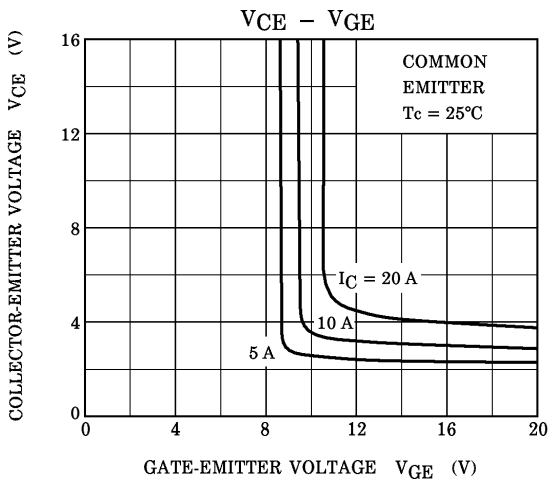
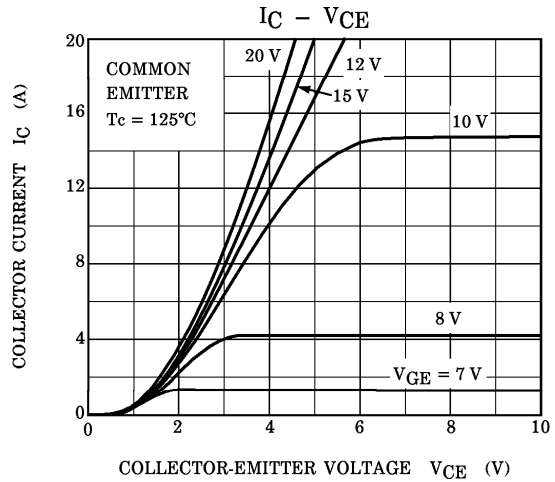
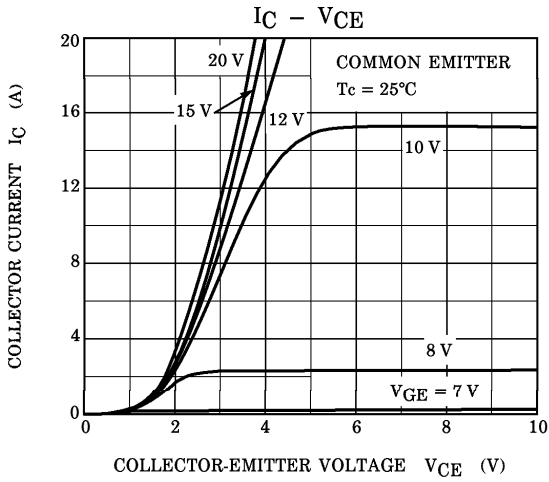
c. Thermistor

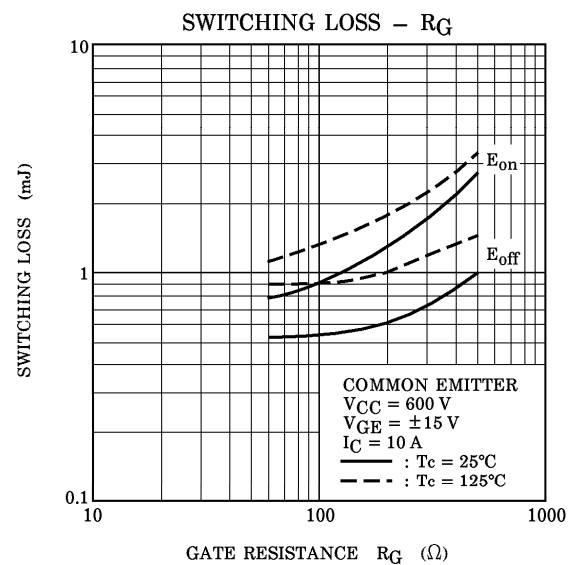
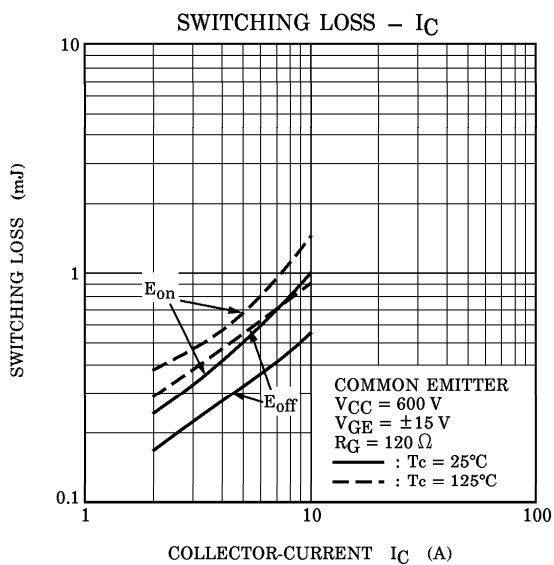
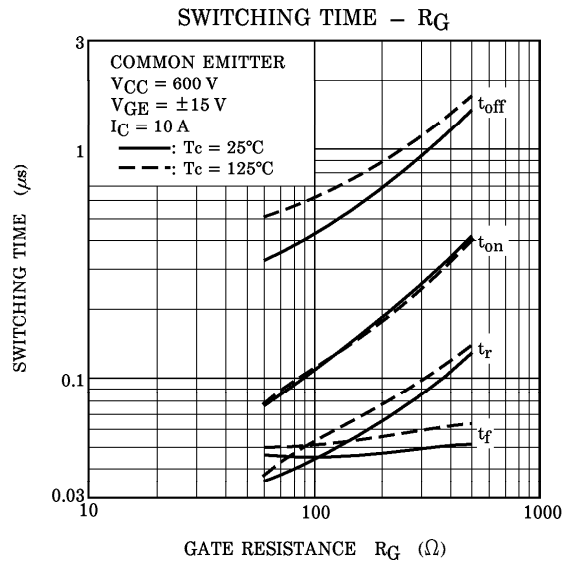
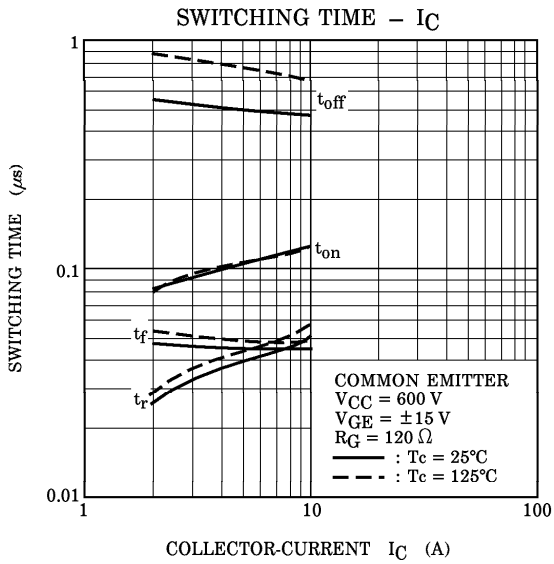
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zero-power Resistance		R_{25}	$I_{TM} = 0.2\text{ mA}, T_c = 25^\circ\text{C}$	17.31	20	23.14	k Ω
B Value		$B_{25/85}$	$T_c = 25^\circ\text{C}/T_c = 85^\circ\text{C}$	—	3760	—	K

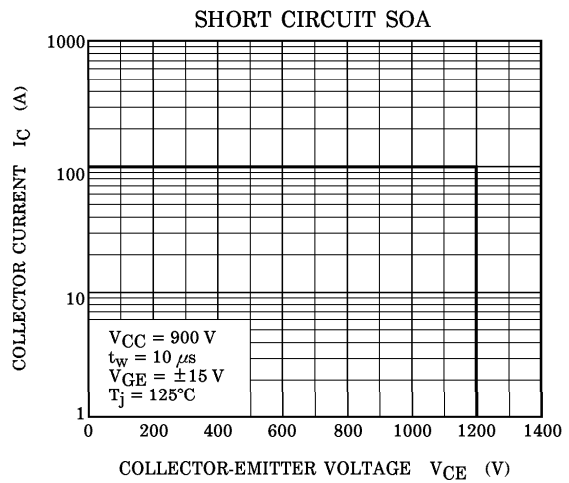
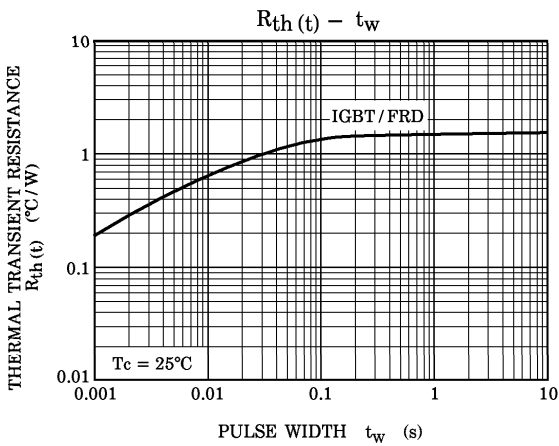
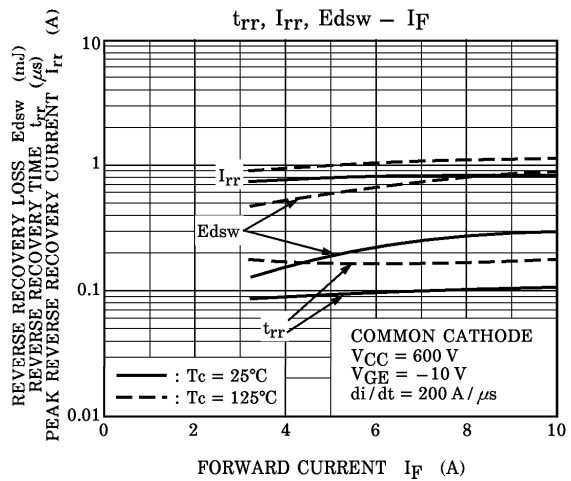
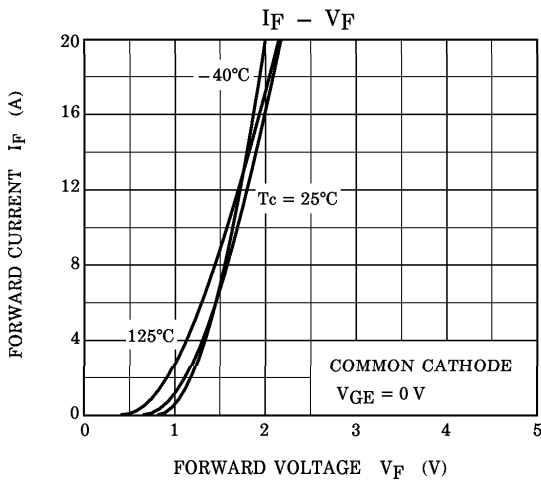
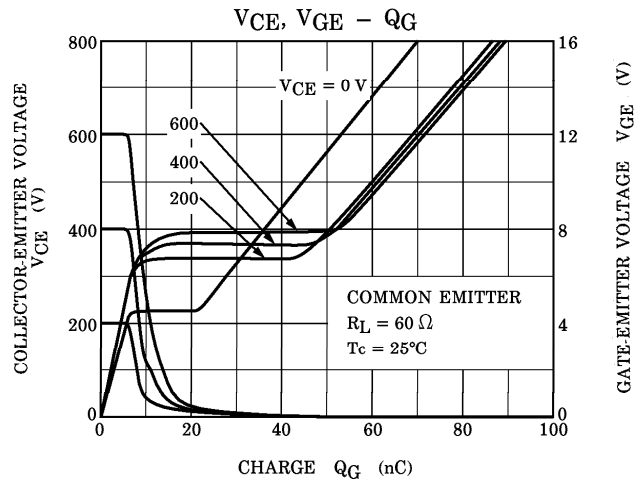
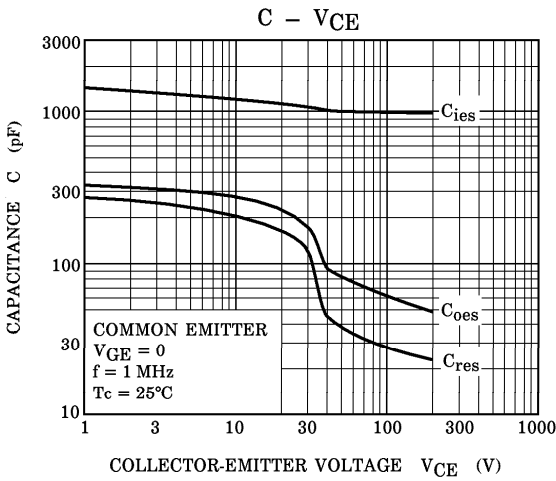
(Note 1) Switching Time Test Circuit & Timing Chart

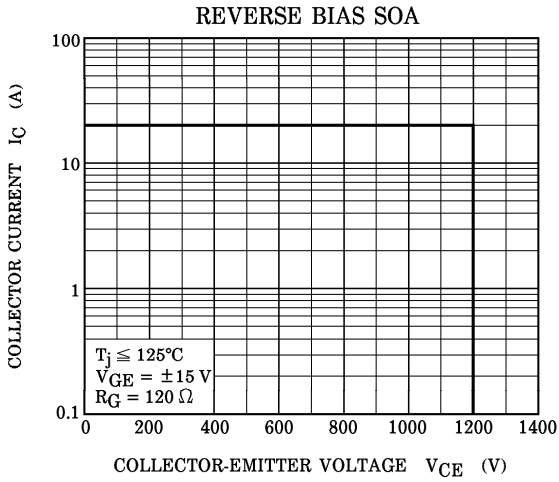


a. Inverter stage









b. Converter stage

